

#### **Differential Hall Sensor**

#### TLE4925/TLE4925C

#### **Features**

- Advanced performance by dynamic self calibration principle
- High sensitivity
- Single chip solution
- Symmetrical thresholds
- High resistance to Piezo effects
- South and north pole pre-induction possible
- low cut-off frequency
- Digital output signal
- Two-wire and three-wire configuration possible
- Wide operating temperature range
- Fast start-up time
- Large operating air-gaps
- Reverse voltage protection at Vs- PIN
- Short- circuit and over temperature protection of output
- No external filter capacitor required (TLE4925C)
- Digital output signal (voltage interface)
- Module style package with two 4.7nF integrated capacitors (TLE4925C)



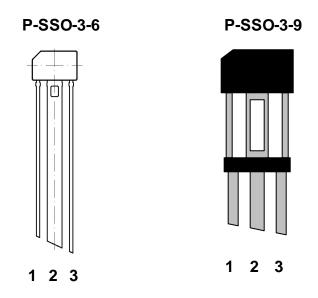


Figure 1: Pin configuration in P-SSO-3-6 and P-SSO-3-9

Pin No.	Symbol	Function
1	$V_{S}$	Supply Voltage
2	GND	Ground
3	Q	Open Drain Output

#### **General Information**

The TLE4925/TLE4925C is an active Hall sensor suited to detects the motion and position of ferromagnetic and permanent magnet structures. An additional self-calibration module has been implemented to achieve optimum accuracy during normal running operation. It comes in a three-pin package for the supply voltage and an open drain output.

#### **Functional Description**

The differential Hall sensor IC detects the motion and position of ferromagnetic and permanent magnet structures by measuring the differential flux density of the magnetic field. To detect ferromagnetic objects the magnetic field must be provided by a back biasing permanent magnet (south or north pole of the magnet attached to the rear unmarked side of the IC package).



Offset cancellation is achieved by advanced digital signal processing. Immediately after power-on motion is detected (start-up mode). After a few transitions the sensor has finished self-calibration and switches to a high-accuracy mode (running mode). In running mode switching occurs at signal zero-crossing of the arithmetic mean of max and min value of magnetic differential signal.  $\Delta B$  is defined as difference between hall plate 1 and hall plate 2.

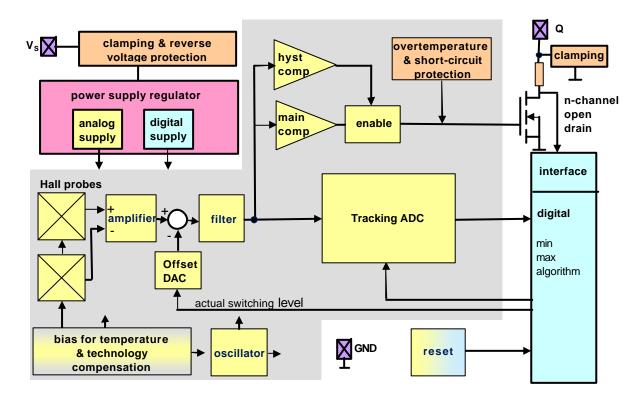


Figure 2: Block Diagram of TLE4925/TLE4925C

#### **Circuit Description**

The TLE4925/TLE4925C is comprised of a supply voltage regulator, a pair of hall probes, spaced at 2.5mm, differential amplifier, noise-shaping filter, comparator, advanced digital signal processor (DSP), A/D and D/A converter and an open drain output.

#### Startup mode:

The differential signal is digitized in the A/D converter and fed into the dsp part of the circuit. There a rising or falling transition is detected and the output stage is triggered accordingly. As the signal is not offset compensated at this time, the output does not neccessarily switch at zero-crossing of the magnetic signal. Signal peaks are also detected in the digital circuit and their arithmetic mean value can be calculated. The offset of this mean value is determined and fed into the offset cancellation DAC. This procedure can be repeated with increasing accuracy. After few increments the IC is switched into the high accuracy running mode.



### Running mode:

In running mode the output is triggered by the comparator. An offset cancellation feedback loop is formed by the A/D converter, dsp and offset cancellation D/A converter. In running mode switching always occurs at zero-crossing. It is only affected by the (small) remaining offset of the comparator and by the remaining propagation delay time of the signal path, mainly determined by the noise-shaping filter. Nevertheless signals below a defined threshold are not detected to avoid unwanted parasitic switching.

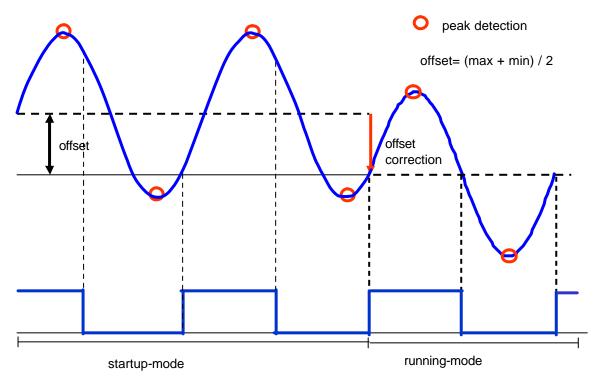


Figure 3: Startup of the device

At transition from startup-mode to running mode switching timing is moving from low-accuracy to high accuracy zero-crossing.



## 1.1 Absolute Maximum Ratings

1.1.1       Supply voltage       V <sub>S</sub> -18       18       V       -1       11       11       11       11       11       12       V       11       11       11       11       11       11       11       11       12       Supply current       I <sub>S</sub> -10       25       mA       -       -       11       11       11       11       11       11       11       12       5       mA       -       -       11       11       11       11       11       12       mA       -       -       -       11       11       11       12       mA       -       -       -       11       11       11       11       11       11       12       mA       -       -       -       11       11       12       ma       -       -       -       12       12       14       14       ma       -       -       14       15       -	No.	Parameter	Symbol	min	Тур	max	Unit	Remarks
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	1.1.1	Supply voltage	Vs	-18		18	V	-
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				-24		24	V	1h with $R_{\text{Series}} \ge 200\Omega^1$
1.1.2       Supply current       Is       -10       25       mA       -         1.1.3       Output OFF voltage       VQ       -0.3       18       V       -         -0.3       26       V       5min with R <sub>Load</sub> ≥ 500Ω       1h (protected by internal series resistor)         1.1.4       Output ON voltage       VQ       -       16       V       Current internal limited by short circuit protection (72h @ T <sub>A</sub> < 40°C).				-26		26	V	5min with $R_{\text{Series}} \ge 200\Omega^1$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				-28		28	V	1min with $R_{Series} \ge 200\Omega^1$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	1.1.2	Supply current	I <sub>S</sub>	-10		25	mA	-
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	1.1.3	Output OFF voltage	$V_Q$	-0.3		18	V	-
1.1.4 Output ON voltage  Volta				-0.3		24	V	1h with $R_{Load} \ge 500\Omega$
1.1.4   Output ON voltage				-0.3		26	V	5min with $R_{Load} \ge 500\Omega$
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				-1.0		-	V	1h (protected by internal
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$								series resistor)
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	1.1.4	Output ON voltage	$V_{Q}$	-		16	V	Current internal limited by
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$								short circuit protection
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$								(72h @ T <sub>A</sub> < 40°C).
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				-		18	V	Current internal limited by
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$								short circuit protection
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$								(1h @ T <sub>A</sub> < 40°C).
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				-		24	V	Current internal limited by
1.1.5 Continuous output current  1.1.6 Junction temperature  T <sub>j</sub> -40  155  °C  2000h (not additive)  165  °C  1000h (not additive)  175  °C  168 h (not additive)  195  °C  3 x1 h (additive to the other life times).  1.1.7 Storage temperature  T <sub>S</sub> -40  150  °C  3 x1 h (additive to the other life times).  1.1.8 Thermal resistance junction-air for P-SSO-3-6								short circuit protection
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$								(1min @ T <sub>A</sub> < 40°C).
1.1.6 Junction temperature  T <sub>j</sub> -40  155  °C  2000h (not additive)  165  °C  1000h (not additive)  175  °C  168 h (not additive)  195  °C  3 x1 h (additive to the other life times).  1.1.7 Storage temperature  T <sub>S</sub> -40  150  °C  -  1.1.8 Thermal resistance junction-air for P-SSO-3-6  P-SSO-3-6	1.1.5	Continuous output	lα	-50		50	mA	-
155 °C 2000h (not additive) 165 °C 1000h (not additive) 175 °C 168 h (not additive) 195 °C 3 x1 h (additive to the other life times).  1.1.7 Storage temperature T <sub>S</sub> -40 150 °C -  1.1.8 Thermal resistance junction-air for P-SSO-3-6    Town of the possible of the possible of the possible with overmoulded devices.		current						
165 °C 1000h (not additive) 175 °C 168 h (not additive) 195 °C 3 x1 h (additive to the other life times).  1.1.7 Storage temperature T <sub>S</sub> -40 150 °C -  1.1.8 Thermal resistance junction-air for P-SSO-3-6  165 °C 1000h (not additive) 165 °C - 168 h (not additive) 190 °C - 150 °C - 190 K/W Lower values are possible with overmoulded devices.	1.1.6	Junction temperature	T <sub>j</sub>	-40			°C	-
175 °C 168 h (not additive) 195 °C 3 x1 h (additive to the other life times).  1.1.7 Storage temperature T <sub>S</sub> -40 150 °C -  1.1.8 Thermal resistance junction-air for P-SSO-3-6 R <sub>th JA</sub> 190 K/W Lower values are possible with overmoulded devices.						155	°C	2000h (not additive)
195 °C 3 x1 h (additive to the other life times).  1.1.7 Storage temperature T <sub>S</sub> -40 150 °C -  1.1.8 Thermal resistance junction-air for P-SSO-3-6 R <sub>th JA</sub> 190 K/W Lower values are possible with overmoulded devices.						165	°C	1000h (not additive)
1.1.7 Storage temperature T <sub>S</sub> -40 150 °C -  1.1.8 Thermal resistance junction-air for P-SSO-3-6 R <sub>th JA</sub>   190 K/W Lower values are possible with overmoulded devices.						175	°C	168 h (not additive)
1.1.7     Storage temperature     T <sub>S</sub> -40     150     °C     -       1.1.8     Thermal resistance junction-air for P-SSO-3-6     R <sub>th JA</sub> 190     K/W     Lower values are possible with overmoulded devices.						195	°C	3 x1 h (additive to the
1.1.8 Thermal resistance junction-air for P-SSO-3-6 In the state of th								other life times).
junction-air for P-SSO-3-6 with overmoulded devices.	1.1.7	Storage temperature	Ts	-40		150	°C	-
P-SSO-3-6	1.1.8	Thermal resistance	$R_{\text{th JA}}$			190	K/W	Lower values are possible
		junction-air for						with overmoulded devices.
P-SSO-3-9		P-SSO-3-6						
		P-SSO-3-9						

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>&</sup>lt;sup>1</sup> Accumulated life time.



## **1.2 Electro Magnetic Compatibility** - (values depend on R<sub>Series</sub>!)

Ref. ISO 7637-1; see test circuit of figure 4 and 5;

 $\Delta B_{PP}$  = 10mT (ideal sinusoidal signal);  $V_S$ =13.5V  $\pm$  0.5V,  $f_B$ = 1000Hz; T= 25°C;  $R_{Series} \ge 200\Omega$ ;

No.	Parameter	Symbol	Level/typ	Status
1.2.1	Testpulse 1	$V_{EMC}$	IV / -100V	C <sup>2</sup>
	Testpulse 2		IV / 100V	C <sup>2</sup>
	Testpulse 3a		IV / -150V	А
	Testpulse 3b		IV / 100V	А
	Testpulse 4		IV / -7V	А
	Testpulse 5		IV / 86.5V	С

Note: Test criteria for status A: No missing pulse no additional pulse on the IC output signal plus duty cycle and jitter are in the specification limits.

Test criteria for status B: No missing pulse no additional pulse on the IC output signal.

(Output signal "OFF" means switching to the voltage of the pull-up resistor).

Test criteria for status C: One or more parameter can be out of specification during the exposure but returns automatically to normal operation after exposure is removed.

Test criteria for status E: IC destroyed.

Ref. ISO 7637-3; TP 1 and TP 2 ref. DIN 40839-3; see test circuit of figure 4 and 5;

 $\Delta B_{PP} = 10$ mT (ideal sinusoidal signal);  $V_S = 13.5 V \pm 0.5 V$ ,  $f_B = 1000$ Hz; T = 25°C;  $R_{Series} \ge 200 \Omega$ ;

No.	Parameter	Symbol	Level/typ	Status
1.2.2	Testpulse 1	$V_{EMC}$	IV / -30V	Α
	Testpulse 2		IV / 30V	Α
	Testpulse 3a		IV / -60V	Α
	Testpulse 3b		IV / 40V	А

Ref. ISO 11452-3; see test circuit of figure 4 and 5; measured in TEM-cell;

 $\Delta B_{PP} = 4mT$  (ideal sinusoidal signal);  $V_S = 13.5V \pm 0.5V$ ,  $f_B = 200Hz$ ;  $T = 25^{\circ}C$ ;  $R_{Series} \ge 200\Omega$ ;

No.	Parameter	Symbol	Level/max	Remarks
1.2.3	EMC field strength	E <sub>TEM-Cell</sub>	IV / 200V/m	AM=80%, f=1kHz;

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Test condition for the trigger window:  $f_{B-field}=200Hz$ ,  $g_{bc}=4mT$ , vertical limits are  $\pm 200mV$  and

horizontal limits are ±200µs.

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<sup>&</sup>lt;sup>2</sup> According to 7637-1 the supply switched "OFF" for t=200ms. For battery "ON" is valid status "A". Page 6 of 25



#### 1.3 ESD Protection

No.	Parameter	Symbol	max	Unit	Remarks
1.3.1	ESD – protection				According to standard
	P-SSO-3-9	$V_{ESD}$	± 8	kV	EIA/JESD22-A114-B
	P-SSO-3-6		± 6	kV	Human Body Model
					(HBM).

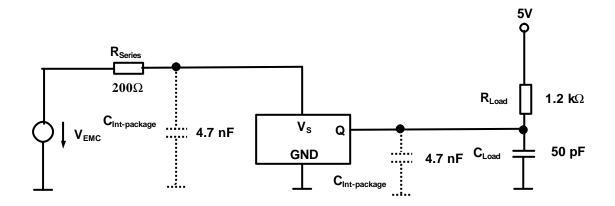


Figure 4: Test Circuit for EMC tests (TLE4925C) – P-SSO-3-9 Package

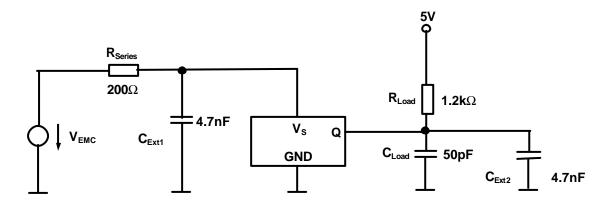


Figure 5: Test Circuit for EMC tests (TLE4925) - P-SSO-3-6 Package



## 2.1 Operating Range

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.1.1	Supply voltage	Vs	3.3		18	V	Continuous
					24	V	1h with $R_{\text{Series}} \ge 200\Omega$
					26	V	5min with R <sub>Series</sub> ≥
							200Ω.
							Extended limits for
							parameters in
							characteristics.
			3			V	During test pulse 4.
2.1.2	Supply voltage ripple	$V_{\text{SAC}}$			6	$V_{pp}$	V <sub>S</sub> =13V; 0 < f < 50kHz
2.1.3	Continuous output OFF	$V_{Q}$	-0.3		18	٧	Continuous
	voltage		-18		24	V	1h with $R_{Load} \ge 500\Omega$
2.1.4	Continuous output ON	$I_Q$	0		20	mA	V <sub>Qmax</sub> =0.6V
	current						
2.1.5	Power on time	t <sub>on</sub>			1	ms	Time to achieve specified accuracy
							After power on the output of the IC is always in high-state.
							After internal resets output is locked <sup>3</sup> .
2.1.6	Operating junction	$T_{j}$	-40			°C	-
	temperature				155	°C	2000 h (not additive)
					165	°C	1000 h (not additive)
					175	°C	168 h (not additive)
							reduced signal
							quality permittable
							(e.g. jitter)

Note: Unless otherwise noted, all temperatures refer to junction temperature. For the supply voltage lower than 28V  $R_{Series} \ge 200\Omega$ ) and junction temperature lower than 195°C the magnetic and AC/DC characteristics can exceed the specification limits.

<sup>&</sup>lt;sup>3</sup> Output of the IC is locked in present state (high-state or low-state) after an internal reset is launched. This reset happens typically every 780ms when there is no significant signal change. See also 2.2.14. A voltage reset causes a release of the output and output is in high state after power on again.



## 2.2 AC/DC Characteristics

Over operating range, unless otherwise specified. Typical values correspond to  $V_S=12V$  and  $T_A=25$ °C

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.2.1	Supply current	I <sub>S</sub>	3	6.8	9	mA	-
2.2.2	Supply current @ 3.3V	I <sub>SVmin</sub>	3	6.7	8	mA	V <sub>S</sub> =3.3V
2.2.3	Supply current @ 24V	I <sub>Smax</sub>	3	7	9.5	mA	V <sub>S</sub> =24V
							$R_{\text{Series}} \geq 200\Omega$
2.2.4	Output saturation	$V_{Qsat}$		0.25	0.6	V	I <sub>Q</sub> = 20mA
	voltage						
2.2.5	Output leakage current	<b>I</b> <sub>Qleak</sub>		0.1	10	μΑ	V <sub>Q</sub> = 18V
2.2.6	Current limit for short-	<b>I</b> <sub>Qshort</sub>	30	60	80	mA	-
	Circuit protection						
2.2.7	Junction temperature	$T_{prot}$	195	210	230	°C	-
	limit for output protection						
2.2.8	Output rise time	t <sub>r</sub> <sup>4</sup>					
	TLE4925C (P-SSO-3-9)		4	12	20	μs	$V_{Load}$ = 4.5 to 24V
							$R_{Load} = 1.2k\Omega;$
							C <sub>Load</sub> = 4.7nF included
							in package.
	TLE4925 (P-SSO-3-6)		4	12	20	μs	$V_{Load} = 4.5 \text{ to } 24V$
							$R_{Load} = 1.2k\Omega;$
							C <sub>Load</sub> = 4.7nF
							external capacitor.
2.2.9	Output fall time	t <sub>f</sub> <sup>5</sup>					
	TLE4925C (P-SSO-3-9)		0.5	0.9	1.3	μs	$V_{Load} = 5V$
			0.65	1.15	1.65	μs	V <sub>Load</sub> = 12V
							$R_{Load} = 1.2k\Omega;$
							C <sub>Load</sub> = 4.7nF included
							in package.
	TLE4925 (P-SSO-3-6)		0.5	0.9	1.3	μs	$V_{Load} = 5V$
			0.65	1.15	1.65	μs	V <sub>Load</sub> = 12V
							$R_{Load} = 1.2k\Omega;$
							C <sub>Load</sub> = 4.7nF
							external capacitor.

<sup>&</sup>lt;sup>4</sup> value of capacitor: 4.7nF±10%; (excluded drift due to temperature); ceramic: X7R; maximum voltage: 100V.



2.2.10	delay time	t <sub>d</sub>	7	12.5	18	μs	Only valid for Tj=25°C.
					20 <sup>6</sup>	μs	Valid for Tj=-40°C till
							Tj=175°C.
							Higher magnetic slopes and overshoots reduce $t_d$ , because the signal is filtered internal.
2.2.11	Temperature drift of	$\Delta t_{\text{d}}$	-6	3 <sup>7</sup>	6	μs	Time over specified
	delay time of output to						temperature range;
	magnetic edge						not additional to t <sub>d</sub>
2.2.12	Frequency range	f	0.001		8	kHz	Operation below 1Hz <sup>8</sup>
2.2.13	Oscillator frequency	f <sub>OSC</sub>	1.08	1.34	1.68	MHz	-
2.2.14	Offset recalibration time after last output change	t <sub>reset</sub>	625	780	970	ms	Output locked to state before recalibration
2.2.15	Clamping voltage	$V_{Sclamp}$	24	27.5		V	$I_S = 20 \text{mA} < 5 \text{min}.$
	V <sub>s</sub> -Pin						
2.2.16	Clamping voltage Q- Pin	$V_{Qclamp}$	24	27.5		V	I <sub>Q</sub> = 20mA < 5min.
2.2.17	Analog reset voltage	$V_{sReset}$		2.35	2.9	V	-

Note: The listed AC/DC and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at  $T_i = 25$  °C and  $V_S = 12$  V.

## 2.3 Magnetic Characteristics in Running Mode

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.3.1	Bias preinduction	B <sub>0</sub>	-500		500	mT	-
2.3.2	Differential bias induction	$\Delta B_0$	-30		30	mT	-
2.3.3	Minimum signal	$ _{\Delta B_{min}} $	0.55		1.5	mT	9
	amplitude						
2.3.4	Maximum signal	$ \Delta B_{max} $			100	mT	Additional to B <sub>0</sub> <sup>10</sup>
	amplitude						
2.3.5	Resistivity against	$ _{\Delta B_{min}} $	-0.2		0.2	mT	F= 2N
	mechanical stress (piezo)						

<sup>&</sup>lt;sup>5</sup> see footnote 6.

<sup>&</sup>lt;sup>6</sup> only valid for the falling edge.

<sup>&</sup>lt;sup>7</sup> related to Tj= 175°C.

 $<sup>^{8}</sup>$  output will switch if magnetic signal is changing more that  $2x \left| \Delta B_{min} \right|$  within offset recalibration time even below 1Hz once per magnetic edge

<sup>&</sup>lt;sup>9</sup> includes also former B<sub>m</sub> of TLE4941-2.

<sup>&</sup>lt;sup>10</sup> exceeding this limit might result in decreased duty cycle performance. With higher values the internal measured signal will be clipped. This will decrease the phase accuracy.



Note: The listed characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not otherwise specified, typical characteristics apply at T<sub>=</sub>25°C and the given supply voltage.

#### 3.1 Self-calibration Characteristics

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
3.1.1	No. of transitions for signal output at startup (startup mode)	n <sub>Start</sub>			2	-	-
3.1.2	No. of transitions for entering running mode	n <sub>Calib</sub>			7	-	Low accuracy of switching timing permitted
3.1.3	Duty cycle in running mode <sup>11</sup>	Dty	45 <sup>7</sup>	50 <sup>7</sup>	55 <sup>7</sup>	%	$\Delta B_{PP}$ = 10mT ideal sinusoidal input signal (T <sub>j</sub> =25°C)
			40 <sup>7</sup>	50 <sup>7</sup>	60 <sup>7</sup>	%	$\Delta B_{PP}$ = 10mT ideal sinusoidal input signal $(-40^{\circ}C \le T_j < 175^{\circ}C)$
3.1.4	Signal jitter in running mode; 1 sigma value <sup>7</sup>	σ1		≤±0.11 <sup>12</sup>		%	$\Delta B_{PP}$ = 10mT ideal sinusoidal input signal; T <sub>j</sub> <150°C
		σ2		≤ ±0.16 <sup>8</sup>		%	$\Delta B_{PP}$ = 10mT ideal sinusoidal input signal; 150°C $\leq$ T <sub>j</sub> $<$ 175°C
3.1.5	Signal Jitter in running mode at power supply of Vs=13V and ripple ±3V; 1 sigma value*	σ3		≤ ±0.11		%	$\Delta B_{PP}$ = 10mT ideal sinusoidal input signal; T <sub>j</sub> <150°C

 $<sup>^{11}</sup>$  this corresponds to a  $\Delta B_0 =$  0mT (magnetic offset).  $^{12}$  typical half value of TLE4941-2 performance (depends largely on  $|\Delta B_{min}|$  and also on f).





3.1.6	Effective noise value of	$B_{neff}$		25		μΤ	$T_j = 25$ °C; The
	the magnetic switching						magnetic noise is
	points						normal distributed,
							nearly independent to
							frequency and without
							sampling noise or
							digital noise effects.
							The effective value
							corresponds to
							1σ probability of
							normal distribution.
							Consequently a 3σ
							value corresponds to
							0.3% probability of
							appearance.
					70	μΤ	Typical value
							corresponds to 1σ.
							Max value corresponds
							to 1σ values in the full
							temperature range and
							include technological
							spreads.
3.1.7	Phase error in startup				≤ ±55	0	$\Delta B_{PP}$ = 10mT ideal
	mode						sinusoidal input
							signal; <sup>13</sup>
3.1.8	Frequency distribution of		Jitter	shall be dist	ributed		-
	signal jitter		li	ike white nois	se		

<sup>&</sup>lt;sup>13</sup> smaller phase errors are possible at higher signal amplitudes, because sinus signal changes to a more rectangle signal.



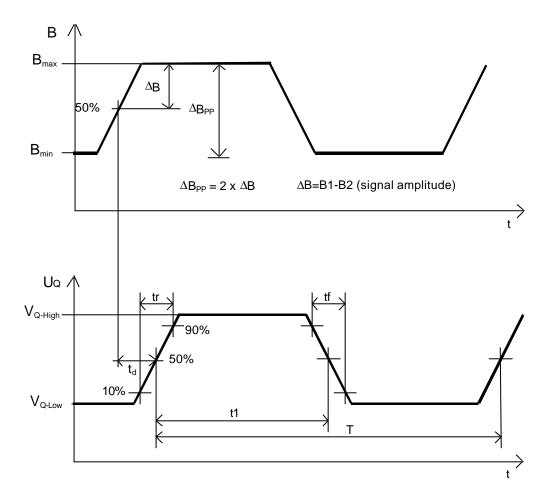
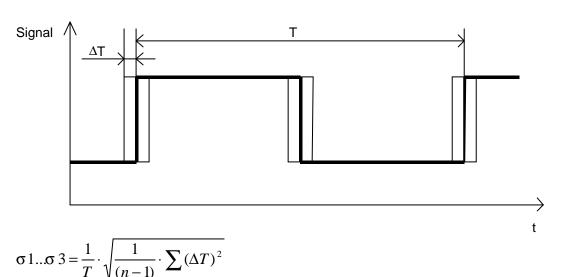


Figure 6 Switching direction



measurement condition:  $n \ge 1000$ 

Figure 7 Definition of signal jitter



### **Application Configurations**

Two possible applications are shown in **Figure 8** and **Figure 9** (Toothed and Magnet Wheel).

The difference between two-wire and three-wire application is shown in **Figure 12** for the TLE4925C and in **Figure 13** for the TLE4925.

## **Gear Tooth Sensing**

In the case of ferromagnetic toothed wheel application the IC has to be biased by the south or north pole of a permanent magnet (e.g.  $SmCO_5$  (Vacuumschmelze VX145)) with the dimensions 8 mm  $\times$  5 mm  $\times$  3 mm) which should cover both Hall probes.

The maximum air gap depends on

- the magnetic field strength (magnet used; pre-induction) and
- the toothed wheel that is used (dimensions, material, etc.; resulting differential field).

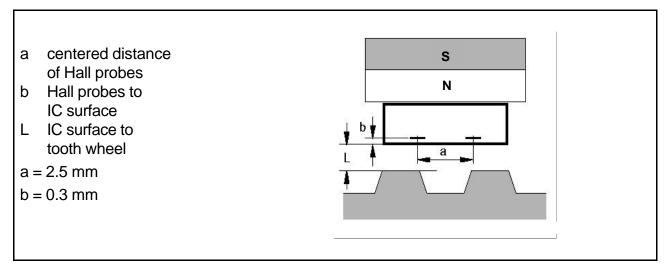


Figure 8 Sensor Spacing

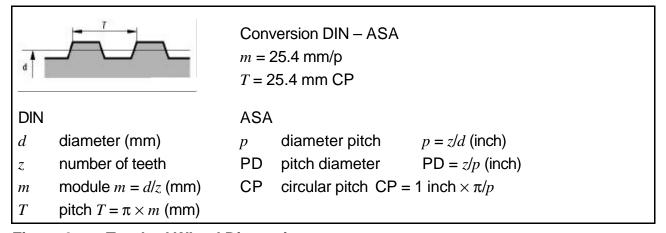


Figure 9 Toothed Wheel Dimensions



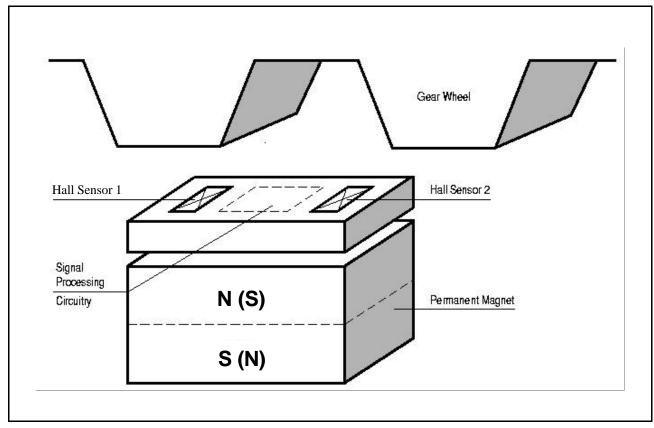


Figure 10 TLE4925/TLE 4925C, with Ferromagnetic Toothed Wheel

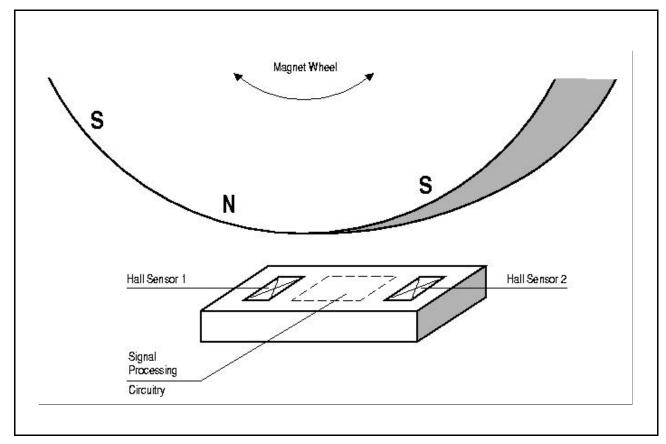




Figure 11 TLE4925/TLE 4925C, with Magnet Wheel

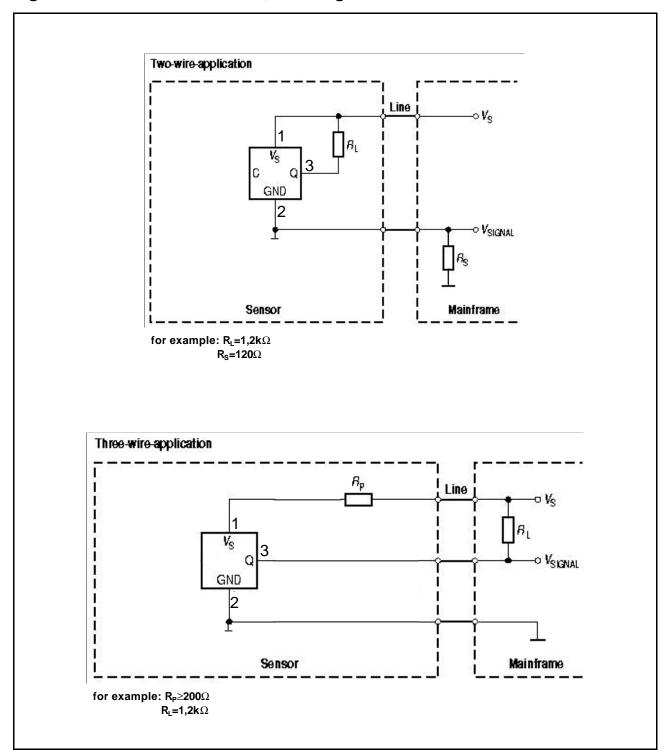


Figure 12 Application Circuits TLE4925C



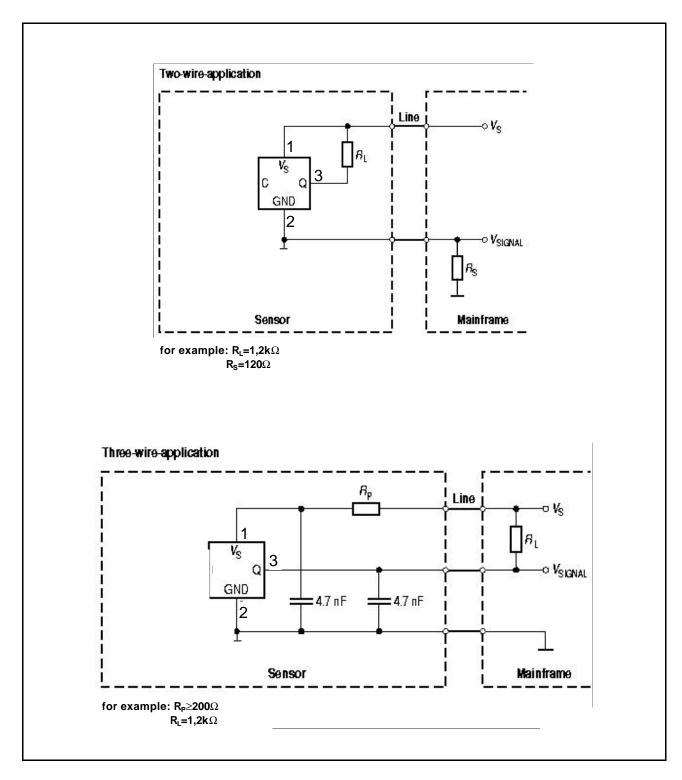


Figure 13 Application Circuits TLE4925



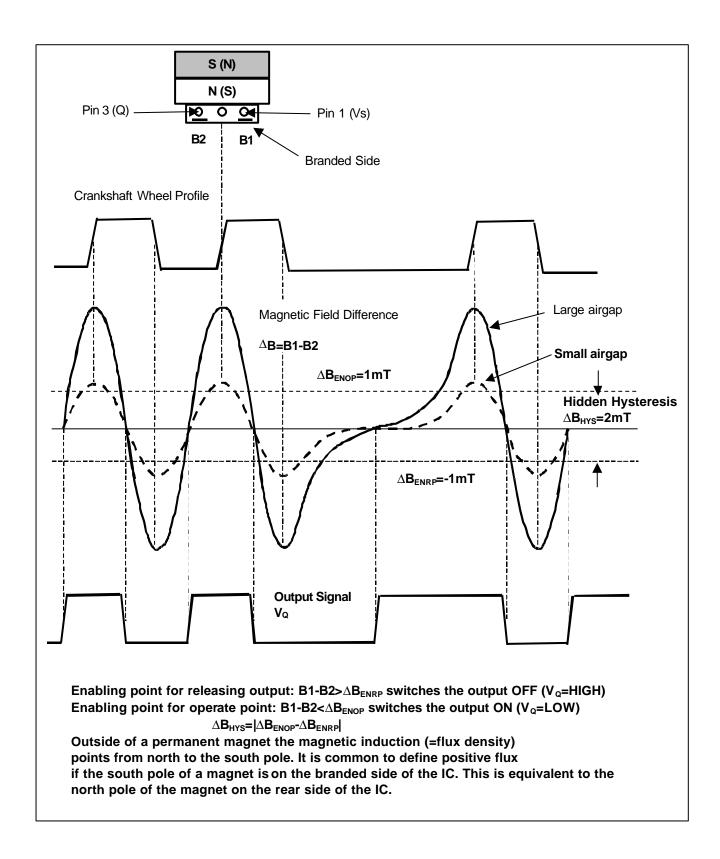


Figure 14 System Operation with hidden hysteresis



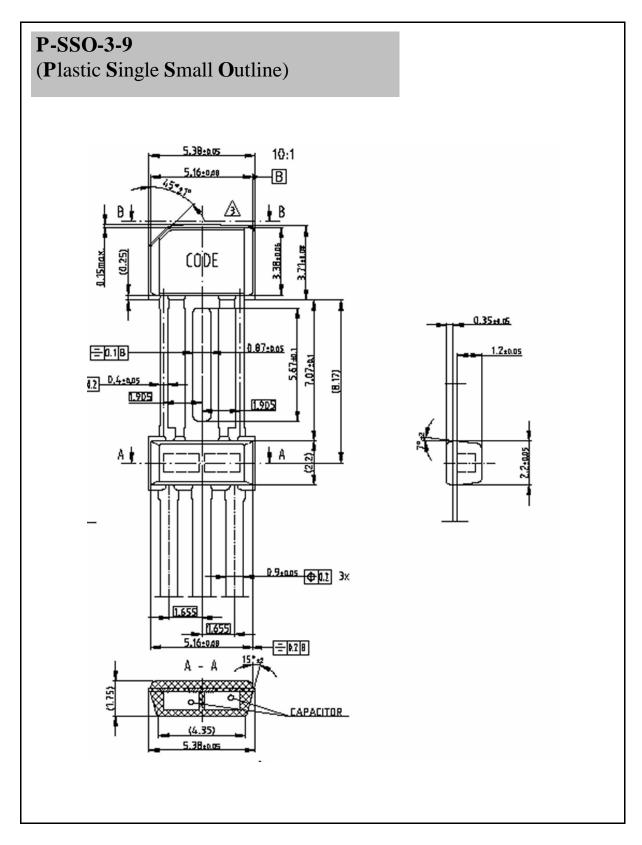


Figure 15 Package Dimensions (P-SSO-3-9)



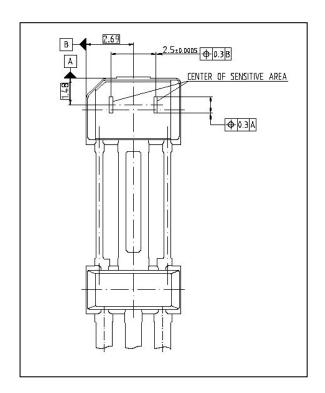


Figure 16 Hall probe spacing in the P-SSO-3-9 package

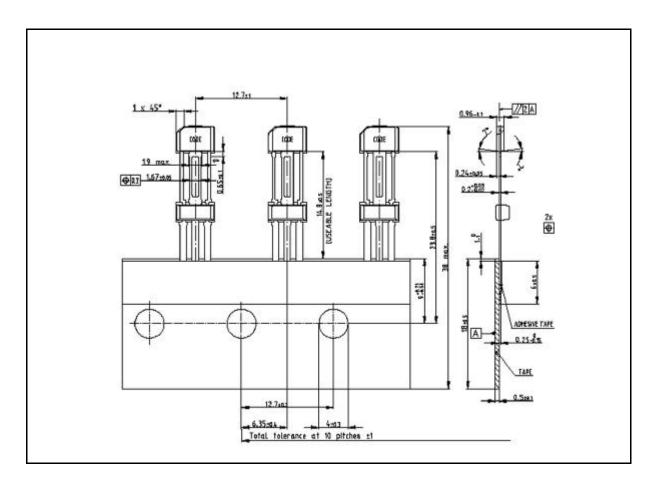
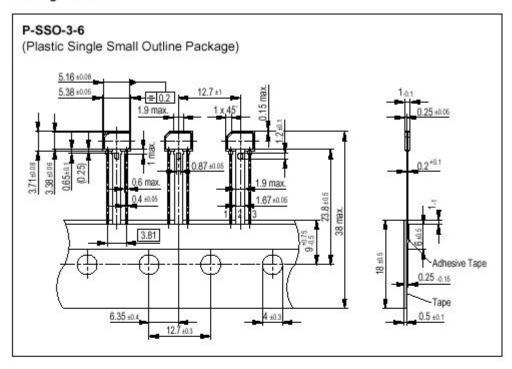


Figure 17 Tape Loading Orientation in the P-SSO-3-9 package



#### **Package Outlines**



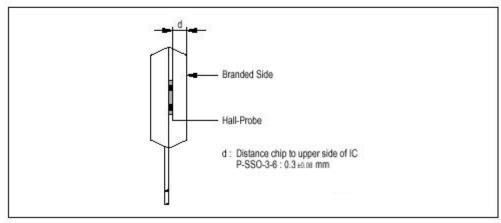


Figure 18 Tape Loading Orientation in the P-SSO-3-6 package



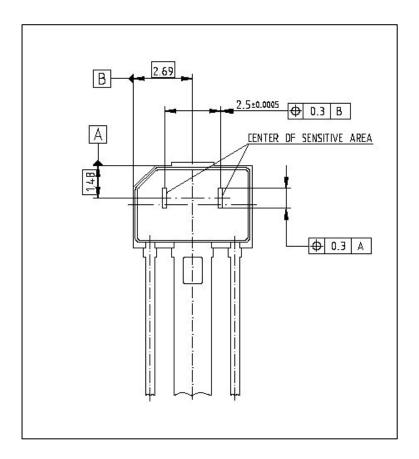
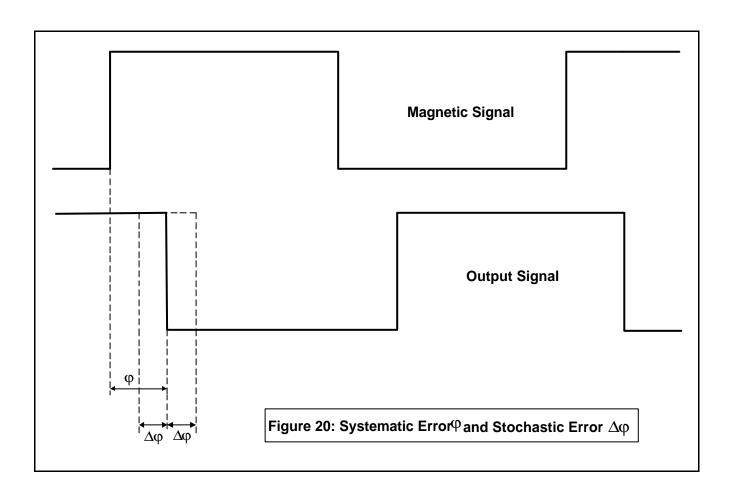


Figure 19 Hall probe spacing in the P-SSO-3-6 package



## **Appendix:**

## Calculation of mechanical errors:



# Systematic Phase Error $\phi$

The systematic error comes in because of the delay-time between the threshold point and the time when the output is switching. It can be calculated as follows:

$$\varphi = \frac{360^{\circ} \bullet n}{60} \bullet t_d$$

 $\phi$  ... systematic phase error in  $^\circ$ 

n ... speed of the camshaft-wheel in min-1

t<sub>d</sub> ... delay time (see specification) in sec



#### Stochastic Phase Error $\Delta \phi$

The stochastic phase error includes the error due to the variation of the delay time with temperature and the error caused by the resolution of the threshold. It can be calculated in the following way:

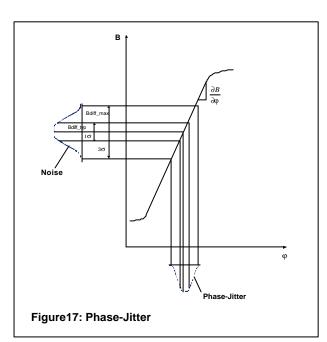
$$\Delta \varphi_d = \frac{360^{\circ} \bullet n}{60} \bullet \Delta t_d$$

 $\Delta \phi_{
m d}$  ... stochastic phase error due to the variation of the delay time over temperature in  $^{\circ}$ 

n ... speed of the camshaft wheel in min<sup>-1</sup>

 $\Delta t_{\text{d}}$  ... variation of delay time over temperature in  $\emph{sec}$ 

## **Jitter (Repeatability)**



The phase jitter is normally caused by the analogue system noise. If there is an update of the offset-DAC due to the algorithm, what could happen after each tooth, then an additional step in the phase occurs (see description of the algorithm). This is not included in the following calculations. The noise is transformed through the slope of the magnetic edge into a phase error. The phase jitter is determined by the two formulas:

$$\varphi_{\textit{Jitter\_typ}} = \frac{\partial \varphi}{\partial B} \bullet \left( B_{\textit{neff\_typ}} \right)$$

$$\varphi_{\textit{Jitter}\_\text{max}} = \frac{\partial \varphi}{\partial B} \bullet \left( B_{\textit{neff}\_\text{max}} \right)$$

#### **PRELIMINARY**



 $\begin{array}{lll} \phi_{\text{Jitter\_typ}} & \dots & \text{typical phase jitter at Tj=25°C in ° (1Sigma)} \\ \phi_{\text{Jitter\_max}} \dots & \text{maximum phase jitter at Tj=175°C in ° (3Sigma)} \end{array}$ 

 $\frac{\partial \varphi}{\partial x}$  ... inverse of the magnetic slope of the edge in  $^{\circ}/T$ 

 $\partial B$ 

# **Example:**

Assumption:  $n = 4500 \text{ min}^{-1}$ 

 $t_d = 14 \ \mu s$ 

 $\Delta t_d = \pm 3 \ \mu s$ 

 $\frac{\partial B}{\partial \phi} = 3 \text{ mT/}^{\circ}$ 

 $B_{neff\_typ} = \pm 40 \ \mu T$  (1 $\sigma$ -value at Tj=25°C)  $B_{neff\_max} = \pm 210 \ \mu T$  (3 $\sigma$ -value at Tj=175°C)

Calculation:  $\phi = 0.378^{\circ}$  ... systematic phase error

 $\Delta \phi_d = \pm 0.081^{\circ}$  ... stochastic phase error due to delay time variation

 $\phi_{\text{Jitter\_typ}} = \pm 0.013^{\circ}$  ... typical phase jitter (1 $\sigma$ -value at Tj=25°C)  $\phi_{\text{Jitter\_max}} = \pm 0.07^{\circ}$  ... maximum phase jitter (3 $\sigma$ -value at Tj=175°C)